Supporting Information

Realization of an efficient electron source by ultraviolet-light-assisted field emission from a one-dimensional ZnO nanorods/n-GaN heterostructure photoconductive detector

Yiren Chen, a † Zhiwei Zhang, a Hong Jiang, a Zhiming Li, a Guoqing Miao, a Hang Song, *a Liqin Hu, b † and Tailiang Guo *b

a State Key Laboratory of Luminescence and Applications, Changchun Institute of Optics, Fine Mechanics and Physics, Chinese Academy of Sciences, Changchun 130033, People's Republic of China

b College of Physics and Information Engineering, Fuzhou University, Fuzhou 350002, People's Republic of China

† These authors contributed equally.

Corresponding Author

*E-mail: songh@ciomp.ac.cn
Fig. S1. Reciprocal space mapping (RSM) obtained by a high-resolution X-ray diffractometer. (a) The symmetrical RSM around the (0002) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding \(2\theta-\omega\) scanning curve. (b) The asymmetrical RSM around the (105) reflection for as-fabricated n-GaN epilayer. The inset shows its corresponding \(2\theta-\omega\) scanning curve.